

ABSTRACT

A semiconductor device is a P-channel type MOS field effect transistor that comprises; a semiconductor substrate, a gate oxide film positioned on the semiconductor substrate, a gate electrode positioned on the gate oxide film; and two P+ source and drain diffusion areas, each of which has a P- offset area, that are formed in an n-well region of the semiconductor substrate. At least one of the gate electrode, the gate oxide film and the offset areas contains fluorine.